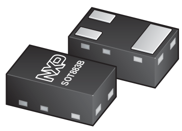


BC847xMB series

45 V, 100 mA NPN general-purpose transistors

Rev. 1 — 5 March 2012 Product data sheet

1. Product profile

1.1 General description

NPN general-purpose transistors in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package			PNP complement
	NXP	JEITA	JEDEC	
BC847AMB	SOT883B	-	-	BC857AMB
BC847BMB	SOT883B	-	-	BC857BMB
BC847CMB	SOT883B	-	-	BC857CMB

1.2 Features and benefits

- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Power dissipation comparable to SOT23
- AEC-Q101 qualified

1.3 Applications

- General-purpose switching and amplification
- Mobile applications

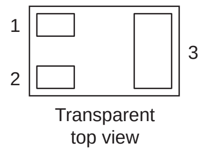
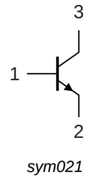
1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	45	V
I_C	collector current		-	-	100	mA
h_{FE}	DC current gain	V_{CE} = 5 V; I_C = 2 mA				
	BC847AMB		110	-	220	
	BC847BMB		200	-	450	
	BC847CMB		420	-	800	

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter		
3	collector		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
BC847xMB series	-	leadless ultra small plastic package; 3 solder lands; body 1.0 × 0.6 × 0.37 mm	SOT883B

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
BC847AMB	0100 0001
BC847BMB	0100 0010
BC847CMB	0100 0011

[1] For SOT883B binary marking code description, see Figure 1.

4.1 Binary marking code description

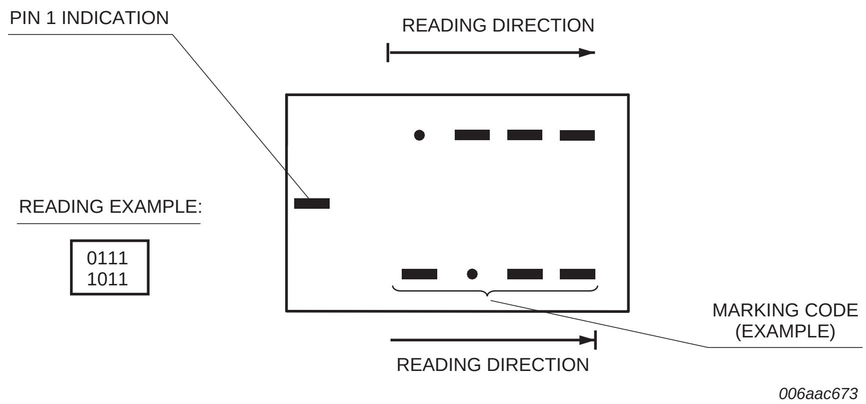


Fig 1. SOT883B binary marking code description

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	45	V
V_{EBO}	emitter-base voltage	open collector		-	6	V
I_C	collector current			-	100	mA
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	200	mA
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms		-	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1][2]	-	250	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			–55	+150	°C
T_{stg}	storage temperature			–65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

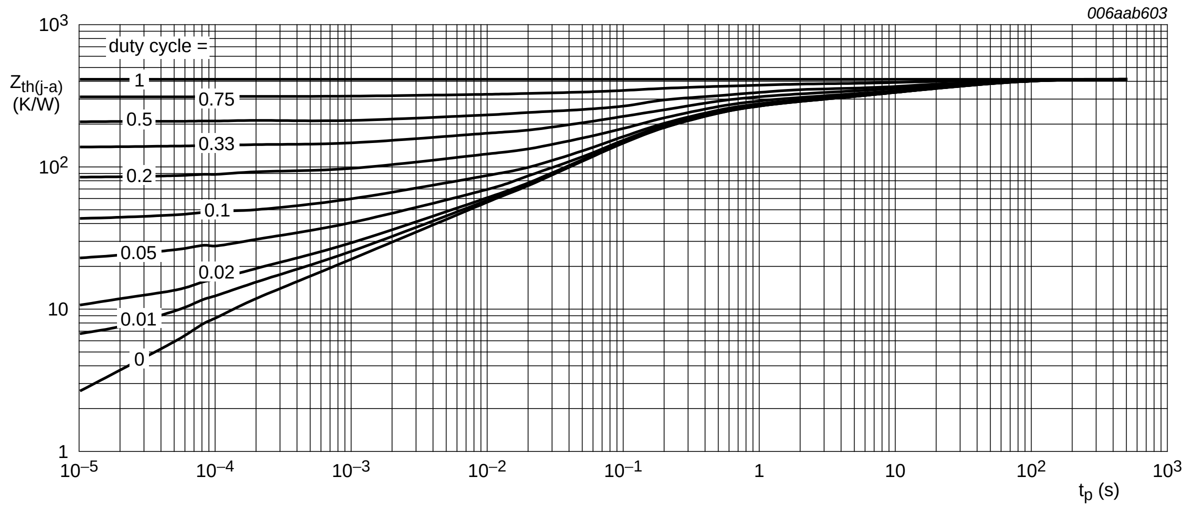
6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

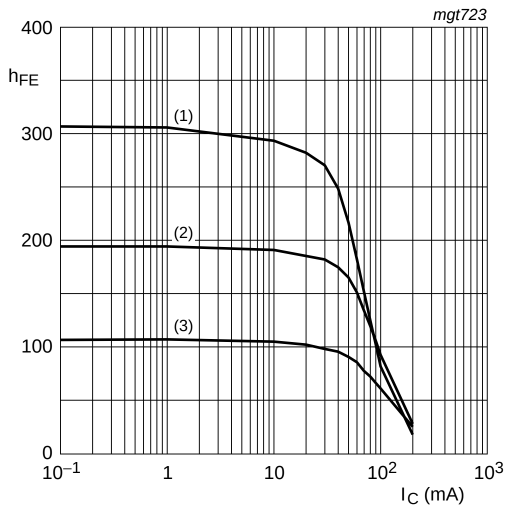
7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	V_{CB} = 30 V; I_E = 0 A		-	-	15	nA
		V_{CB} = 30 V; I_E = 0 A; T_j = 150 °C		-	-	5	μA
I_{EBO}	emitter-base cut-off current	V_{EB} = 5 V; I_C = 0 A		-	-	100	nA
h_{FE}	DC current gain	V_{CE} = 5 V; I_C = 2 mA					
	BC847AMB			110	-	220	
	BC847BMB			200	-	450	
	BC847CMB			420	-	800	
V_{CEsat}	collector-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA		-	90	200	mV
		I_C = 100 mA; I_B = 5 mA	[1]	-	200	400	mV
V_{BEsat}	base-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA		-	700	-	mV
		I_C = 100 mA; I_B = 5 mA	[1]	-	900	-	mV
V_{BE}	base-emitter voltage	I_C = 2 mA; V_{CE} = 5 V		580	660	700	mV
		I_C = 10 mA; V_{CE} = 5 V		-	-	770	mV
f_T	transition frequency	V_{CE} = 5 V; I_C = 10 mA; f = 100 MHz		100	-	-	MHz
C_c	collector capacitance	V_{CB} = 10 V; I_E = i_e = 0 A; f = 1 MHz		-	-	1.5	pF
C_e	emitter capacitance	V_{EB} = 0.5 V; I_C = i_c = 0 A; f = 1 MHz		-	11	-	pF
NF	noise figure	I_C = 200 μA; V_{CE} = 5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz		-	2	10	dB

[1] Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.



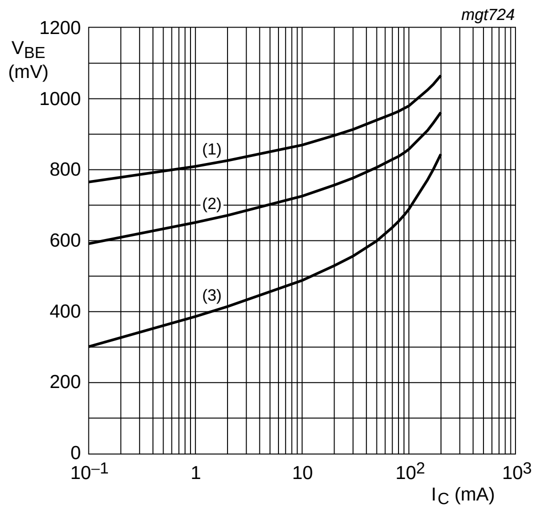
V_{CE} = 5 V

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −55 °C

Fig 3. BC847AMB: DC current gain as a function of collector current; typical values



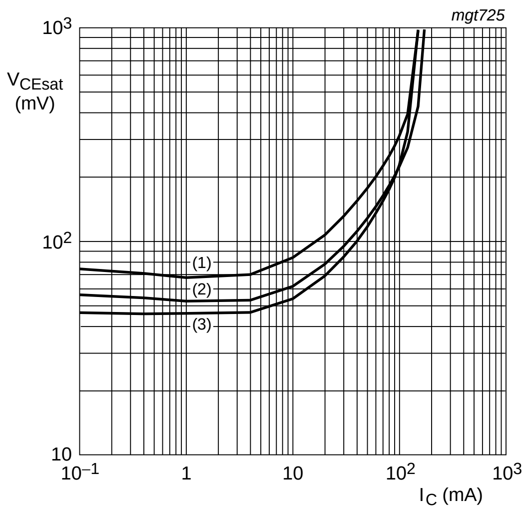
V_{CE} = 5 V

(1) T_{amb} = −55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 150 °C

Fig 4. BC847AMB: Base-emitter voltage as a function of collector current; typical values



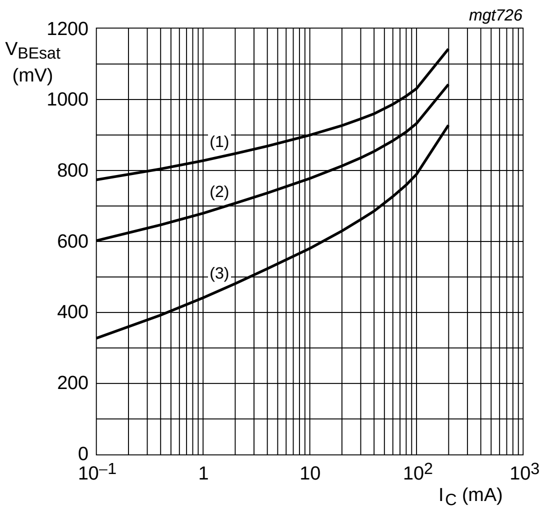
I_C/I_B = 20

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −55 °C

Fig 5. BC847AMB: Collector-emitter saturation voltage as a function of collector current; typical values



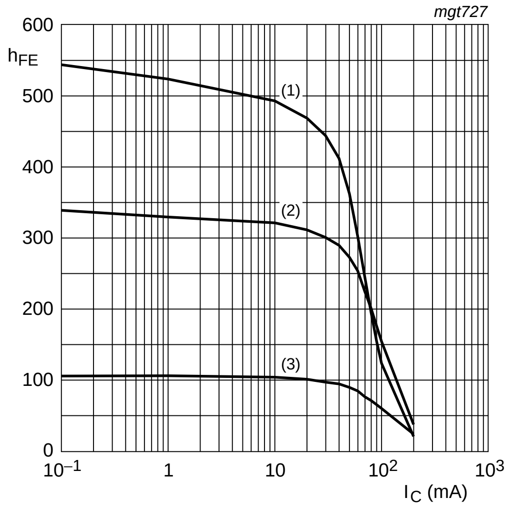
I_C/I_B = 10

(1) T_{amb} = −55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 150 °C

Fig 6. BC847AMB: Base-emitter saturation voltage as a function of collector current; typical values



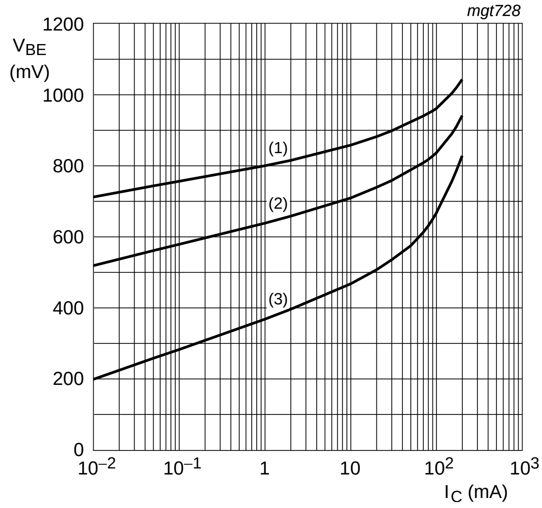
V_{CE} = 5 V

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −55 °C

Fig 7. BC847BMB: DC current gain as a function of collector current; typical values



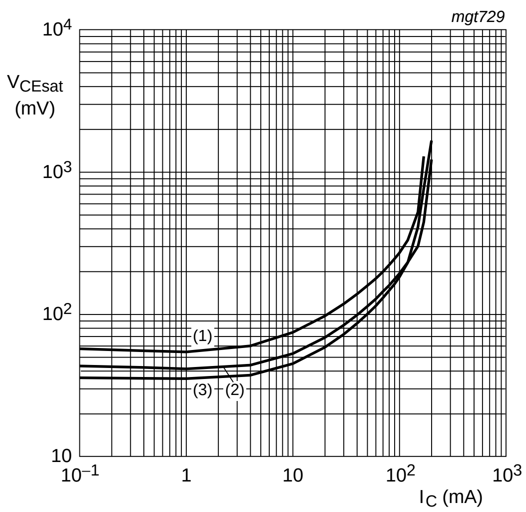
V_{CE} = 5 V

(1) T_{amb} = −55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 150 °C

Fig 8. BC847BMB: Base-emitter voltage as a function of collector current; typical values



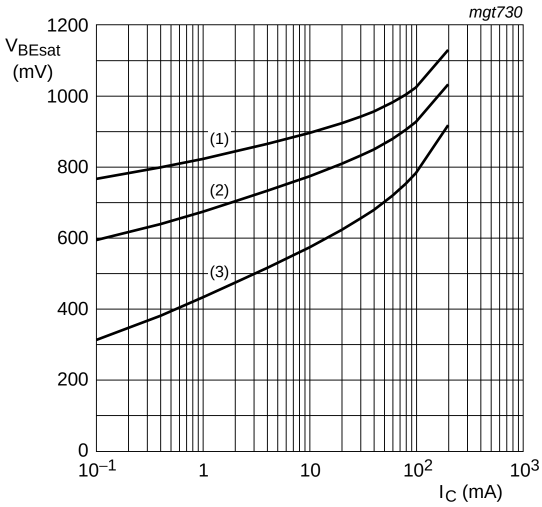
I_C/I_B = 20

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −55 °C

Fig 9. BC847BMB: Collector-emitter saturation voltage as a function of collector current; typical values



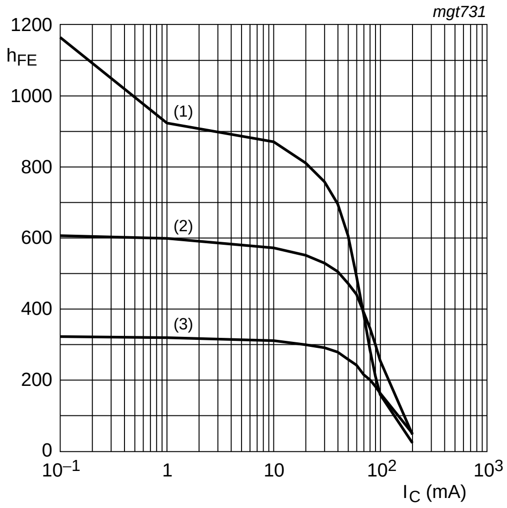
I_C/I_B = 10

(1) T_{amb} = −55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 150 °C

Fig 10. BC847BMB: Base-emitter saturation voltage as a function of collector current; typical values



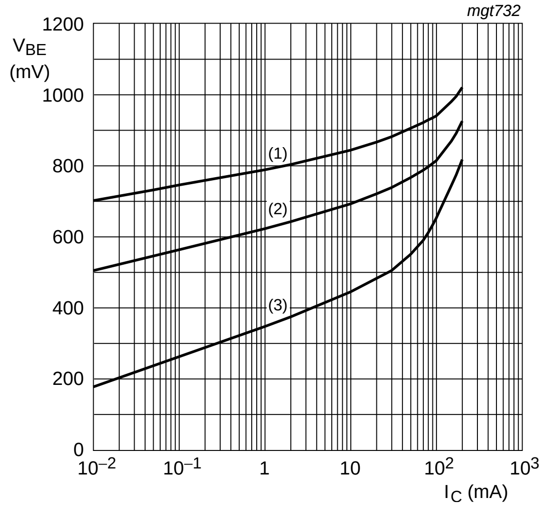
V_{CE} = 5 V

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −55 °C

Fig 11. BC847CMB: DC current gain as a function of collector current; typical values



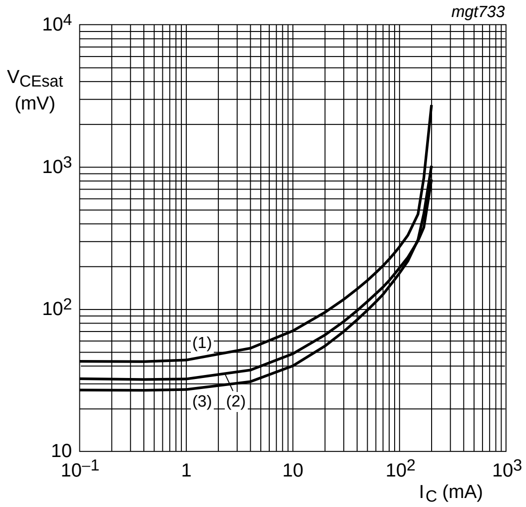
V_{CE} = 5 V

(1) T_{amb} = −55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 150 °C

Fig 12. BC847CMB: Base-emitter voltage as a function of collector current; typical values



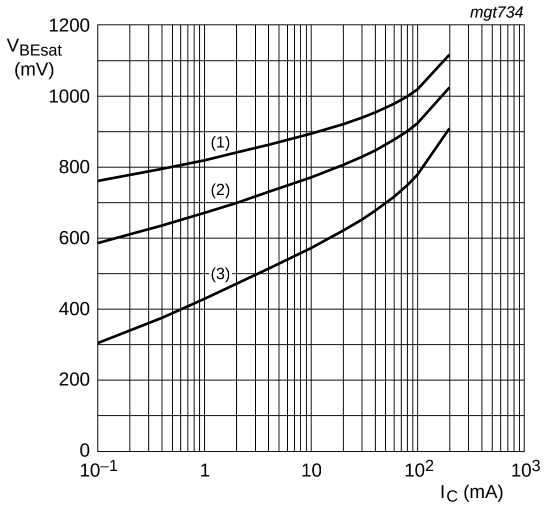
I_C/I_B = 20

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −55 °C

Fig 13. BC847CMB: Collector-emitter saturation voltage as a function of collector current; typical values



I_C/I_B = 10

(1) T_{amb} = −55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 150 °C

Fig 14. BC847CMB: Base-emitter saturation voltage as a function of collector current; typical values

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

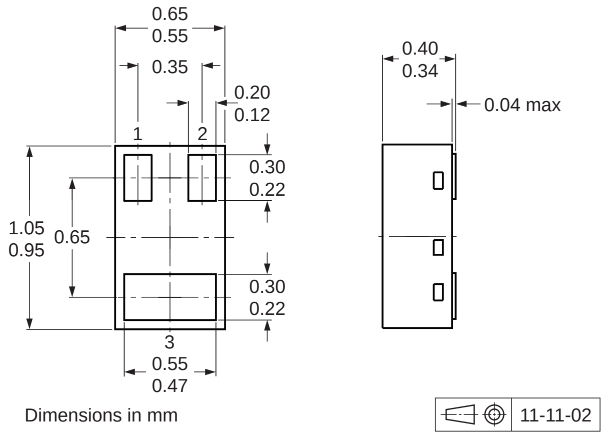


Fig 15. Package outline SOT883B

10. Packing information

Table 9. Packing methods

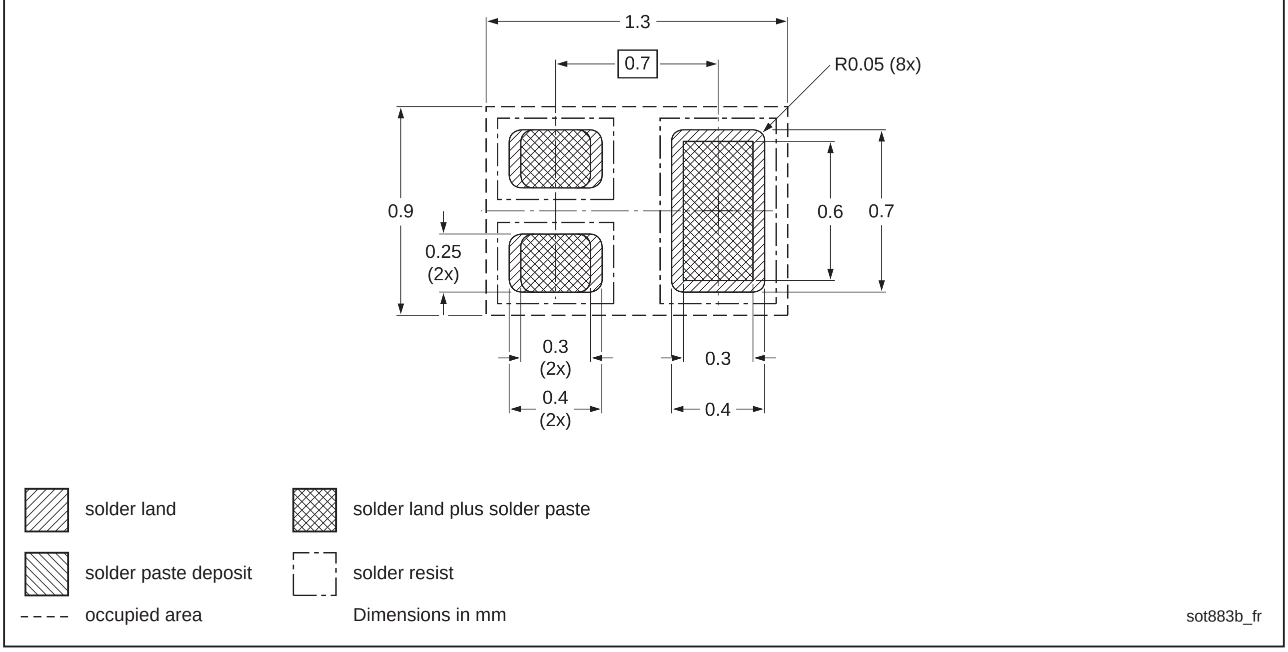
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			10000
BC847xMB series	SOT883B	2 mm pitch, 8 mm tape and reel	-315

[1] For further information and the availability of packing methods, see Section 14.

11. Soldering

Footprint information for reflow soldering **SOT883B**



Reflow soldering is the only recommended soldering method.

Fig 16. Reflow soldering footprint SOT883B

12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC847XMB_SER v.1	20120305	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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14. Contact information

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15. Contents

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